



## DOCUMENT CHANGE REQUEST

DCR number 1080

Changes required for: General

Originator: Jean-Marc Bureau

Date: 2018/12/10

Date sent: 2017/03/30

Organisation: Cobham

Status: IMPLEMENTED

Title: Capacitors, Microwave, Silicon, Naked die, MOS, based on Type 101M, 201M, 400M and 401M

Number: 5711/002

Issue: 3

Other documents affected:

Page:

7

Paragraph:

1.4.2 Component Type Variants and Range of Components

Original wording:

For variants 24 & 27: Rated Voltage UR (V)

Variant 24 / 401M111J : 400 V

Variant 27 / 401M112J : 400 V

Proposed wording:

For variants 24 & 27: Rated Voltage UR (V)

Variant 24 / 401M111J : 200 V

Variant 27 / 401M112J : 200 V

Justification:

Typo error in issues 2 and 3. Was correct in issue 1

Attachments:

N/A

Modifications:

The DCR changes are replaced by the following as agreed with ESA/CNES/Cobham:

Change the Rated Voltage UR in the end column of the Para. 1.4.2 Component Type Variants and Range of Components table (on spec page 7) to be 200V (was 400V) together with the addition of a new Note 2 against the rated voltage field for these 2 Variants as follows:

Note 2: Oxide Nominal Rated Voltage = 400V, and Oxide Breakdown Voltage = 600V, tested only during wafer fabrication.

The following minor editorial change is also added:

- Para. 2.2 wording is amended to "The information to be marked on the primary package shall be as follows:".

Approval signature:

A handwritten signature in cursive script, appearing to read "Austan Rem".

Date signed:

2018-12-10